

### Description

The IRLR2905ZPBF uses advanced trench technology

to provide excellent  $R_{\text{DS}(\text{ON})},$  low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

### **General Features**

V<sub>DS</sub> = 60V I<sub>D</sub> =50 A

 $R_{DS(ON)} < 15m\Omega @ V_{GS}=10V$ 

### Application

Battery protection

Load switch

Uninterruptible power supply

### Package Marking and Ordering Information

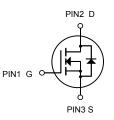
Product ID	Pack	Marking	Qty(PCS)
IRLR2905ZPBF	TO-252-2L	RLR2905 XXXX	2500

### Absolute Maximum Ratings (Tc=25°Cunless otherwise noted)

Symbol	Parameter	Rating	Units
Vds	Drain-Source Voltage	60	V
Vgs	Gate-Source Voltage	±20	V
l₀@Tc=25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	50	А
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	25	А
I₀@T₄=25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	7.4	А
I₀@T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	6	А
Ідм	Pulsed Drain Current <sup>2</sup>	90	А
EAS	Single Pulse Avalanche Energy <sup>3</sup>	39.2	mJ
las	Avalanche Current	28	А
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	45	W
PD@TA=25°C	Total Power Dissipation <sup>4</sup>	2	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
R <sub>0</sub> JA	Thermal Resistance Junction-Ambient <sup>1</sup>	62	°C/W







N-Channel MOSFET



Rejc

# IRLR2905ZPBF

N-Channel Enhancement Mode MOSFET

Thermal Resistance Junction-Case<sup>1</sup>

2.8

°C/W

Electrical Characteristics (T\_J=25  $\degree$ C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	60			V
∆BV <sub>DSS</sub> /∆TJ	BV <sub>DSS</sub> Temperature Coefficient	V <sub>DSS</sub> Temperature Coefficient Reference to 25°C, I <sub>D</sub> =1mA		0.057		V/°C
		V <sub>GS</sub> =10V , I <sub>D</sub> =20A		11	15	
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V , I <sub>D</sub> =10A		15	20	mΩ
VGS(th)	Gate Threshold Voltage		1.2		2.5	V
$\bigtriangleup V_{\text{GS(th)}}$	V <sub>GS(th)</sub> Temperature Coefficient	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA		-5.68		mV/°C
		V <sub>DS</sub> =48V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =48V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			5	uA
lgss	Gate-Source Leakage Current	$V_{GS}$ =±20V , $V_{DS}$ =0V			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =15A		45		S
Rg	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		1.7		Ω
Qg	Total Gate Charge (4.5V)			19.3		
Qgs	Gate-Source Charge			7.1		nC
Qgd	Gate-Drain Charge	_		7.6		
Td(on)	Turn-On Delay Time			7.2		
Tr	Rise Time	V <sub>DD</sub> =30V , V <sub>GS</sub> =10V ,		50		ns
Td(off)	Turn-Off Delay Time	R <sub>G</sub> =3.3 , I <sub>D</sub> =15A		36.4		
T <sub>f</sub>	Fall Time	ID= I 5A		7.6		
Ciss	Input Capacitance			2423		
Coss	Output Capacitance V <sub>DS</sub> =15V , V <sub>GS</sub> =0V ,			145		pF
Crss	Reverse Transfer Capacitance	_		97		
Is	Continuous Source Current <sup>1,5</sup>				35	Α
lsм	Pulsed Source Current <sup>2,5</sup>	−V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			80	Α
Vsd	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =A , T <sub>J</sub> =25°C			1	V
trr	Reverse Recovery Time			16.3		nS
Qrr	Reverse Recovery Charge	IF=15A , dI/dt=100A/µs , Tյ=25°C		11		nC

Note :

1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

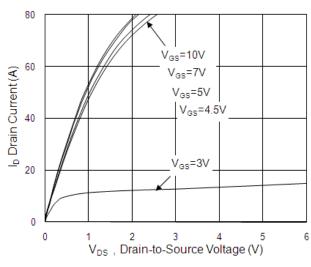
2.The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%

3. The EAS data shows Max. rating . The test condition is VDD=25V, VGS=10V, L=0.1mH, IAS=28A

4. The power dissipation is limited by  $150^{\circ}$  junction temperature 5. The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation



### **Typical Characteristics**



**Fig.1 Typical Output Characteristics** 

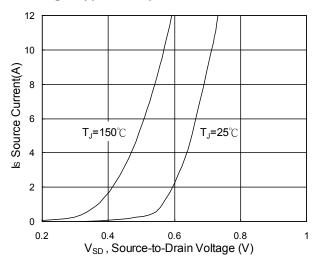


Fig.3 Forward Characteristics of Reverse

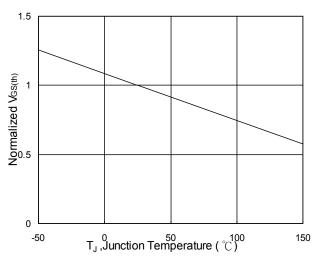


Fig.5 Normalized  $V_{GS(th)} \, v.s \; T_J$ 

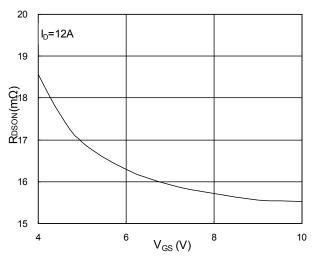


Fig.2 On-Resistance v.s Gate-Source

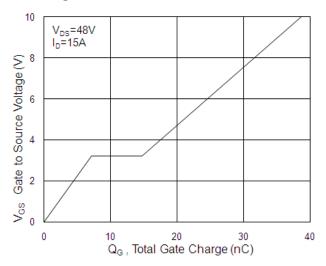


Fig.4 Gate-Charge Characteristics

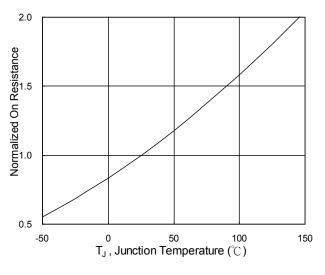


Fig.6 Normalized R<sub>DSON</sub> v.s T<sub>J</sub>



## IRLR2905ZPBF

N-Channel Enhancement Mode MOSFET

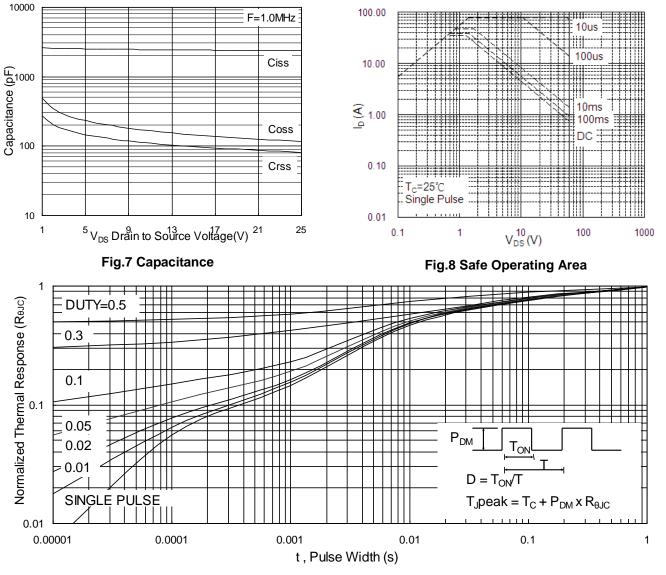


Fig.9 Normalized Maximum Transient Thermal Impedance

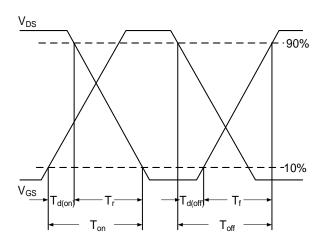


Fig.10 Switching Time Waveform

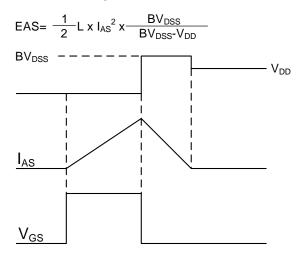
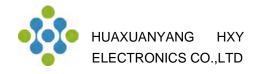
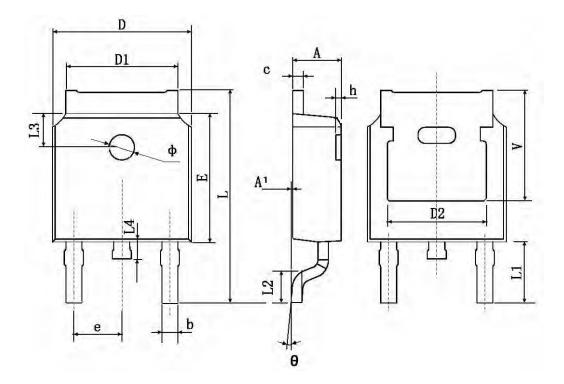


Fig.11 Unclamped Inductive Switching Waveform



## TO-252-2L Package Information



O	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0 °	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	) TYP.	0.211 TYP.		



### **Attention**

Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.

• HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.

• Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could

give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

• In the event that any or all HUA XUAN YANG ELECTRONICS products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

• No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.

Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production.
HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.